

IRFZ34NSPbF IRFZ34NLPbF

HEXFET® Power MOSFET

- Advanced Process Technology
- Surface Mount (IRFZ34NS)
- Low-profile through-hole (IRFZ34NL)
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Lead-Free

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The D²Pak is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D²Pak is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application.

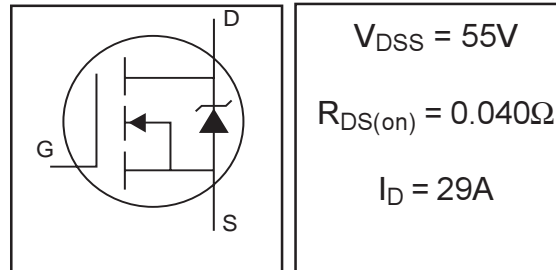
The through-hole version (IRFZ34NL) is available for low-profile applications.

Absolute Maximum Ratings

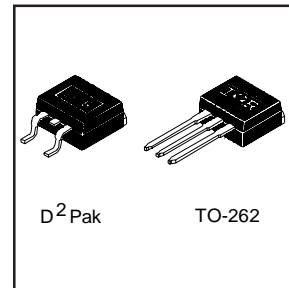
	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$ Ⓞ	29	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$ Ⓞ	20	
I_{DM}	Pulsed Drain Current ① ⑤	100	
$P_D @ T_A = 25^\circ\text{C}$	Power Dissipation	3.8	W
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation	68	W
	Linear Derating Factor	0.45	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy② ⑤	130	mJ
I_{AR}	Avalanche Current④	16	A
E_{AR}	Repetitive Avalanche Energy④	5.6	mJ
dv/dt	Peak Diode Recovery dv/dt ③ ⑤	5.0	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	---	2.2	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB mount) **	---	40	



$V_{DSS} = 55\text{V}$
 $R_{DS(on)} = 0.040\Omega$
 $I_D = 29\text{A}$



D²Pak

TO-262

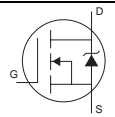
IRFZ34NS/LPbF

International
 Rectifier

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	55	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.052	—	V/°C	Reference to 25°C , $I_D = 1\text{mA}$ ①
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	—	—	0.040	Ω	$V_{GS} = 10V, I_D = 16A$ ②
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
g_{fs}	Forward Transconductance	6.5	—	—	S	$V_{DS} = 25V, I_D = 16A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	$V_{DS} = 55V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 44V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
Q_g	Total Gate Charge	—	—	34	nC	$I_D = 16A$
Q_{gs}	Gate-to-Source Charge	—	—	6.8		$V_{DS} = 44V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	14		$V_{GS} = 10V$, See Fig. 6 and 13 ④⑤
$t_{d(on)}$	Turn-On Delay Time	—	7.0	—	ns	$V_{DD} = 28V$
t_r	Rise Time	—	49	—		$I_D = 16A$
$t_{d(off)}$	Turn-Off Delay Time	—	31	—		$R_G = 18\Omega$
t_f	Fall Time	—	40	—		$R_D = 1.8\Omega$, See Fig. 10 ④⑤
L_S	Internal Source Inductance	—	7.5	—	nH	Between lead, and center of die contact
C_{iss}	Input Capacitance	—	700	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	240	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	100	—		$f = 1.0\text{MHz}$, See Fig. 5 ⑤

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	29	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	100		
V_{SD}	Diode Forward Voltage	—	—	1.6	V	$T_J = 25^\circ\text{C}, I_S = 16A, V_{GS} = 0V$ ②
t_{rr}	Reverse Recovery Time	—	57	86	ns	$T_J = 25^\circ\text{C}, I_F = 16A$
Q_{rr}	Reverse Recovery Charge	—	130	200	nC	$di/dt = 100A/\mu s$ ④⑤
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② $V_{DD} = 25V$, starting $T_J = 25^\circ\text{C}$, $L = 610\mu H$
 $R_G = 25\Omega, I_{AS} = 16A$. (See Figure 12)

③ $I_{SD} \leq 16 A$, $di/dt \leq 420A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$,
 $T_J \leq 175^\circ\text{C}$

④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

⑤ Uses IRFZ34N data and test conditions

** When mounted on 1" square PCB (FR-4 or G-10 Material).

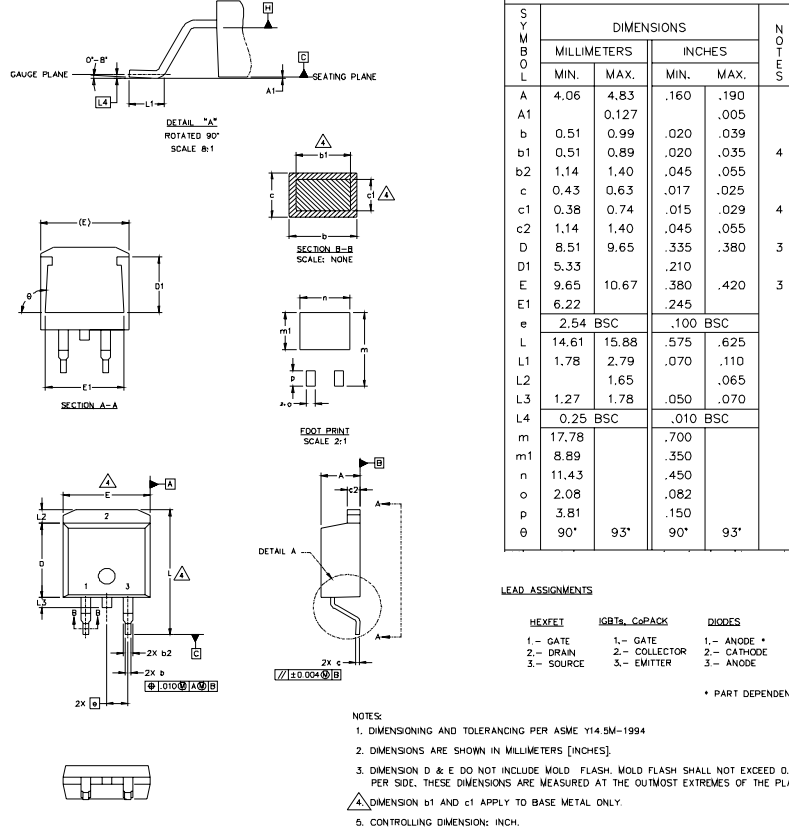
For recommended footprint and soldering techniques refer to application note #AN-994.

IRFZ34NS/LPbF

International
IR Rectifier

D²Pak Package Outline

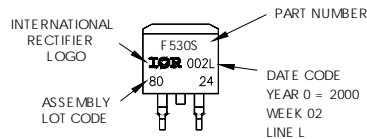
Dimensions are shown in millimeters (inches)



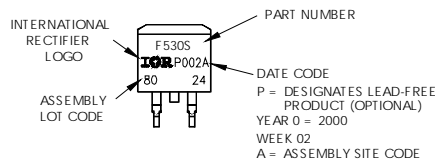
D²Pak Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH
LOT CODE 8024
ASSEMBLED ON WW02, 2000
IN THE ASSEMBLY LINE "L"

Note: "P" in assembly line
position indicates "Lead-Free"



OR

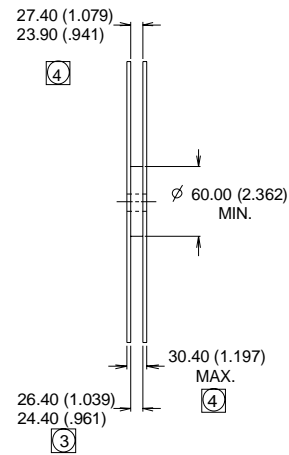
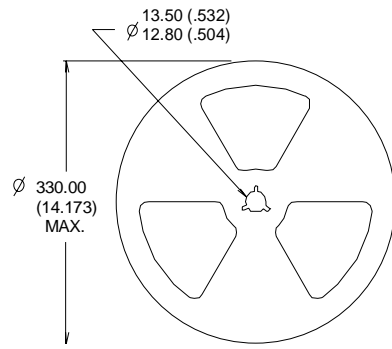
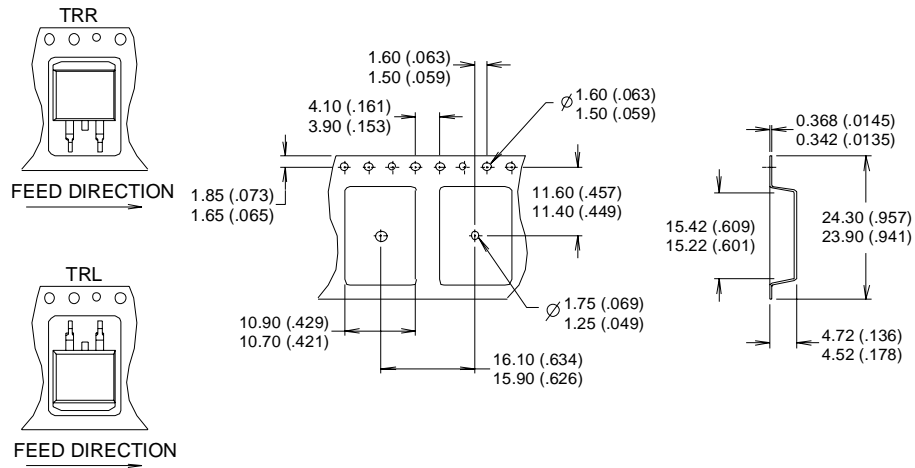


IRFZ34NS/LPbF

International
IR Rectifier

D²Pak Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES:
1. CONFORMS TO EIA-418.
 2. CONTROLLING DIMENSION: MILLIMETER.
 - ③ DIMENSION MEASURED @ HUB.
 - ④ INCLUDES FLANGE DISTORTION @ OUTER EDGE.

Data and specifications subject to change without notice.

International
IR Rectifier